# PROCESS CPD87R

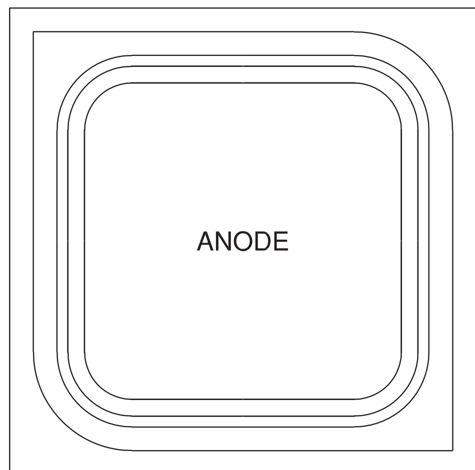
## Schottky Diode

Low Leakage Schottky Diode Chip

### PROCESS DETAILS

| Process | EPITAXIAL PLANAR |
|---|---|
| Die Size | 14.6 x 14.6 MILS |
| Die Thickness | 3.9 MILS |
| Anode Bonding Pad Area | 11.8 x 11.8 MILS |
| Top Side Metalization | Al - 30,000Å |
| Back Side Metalization | Au - 12,000Å |

### GEOMETRY




BACKSIDE CATHODE R0

**GROSS DIE PER 5 INCH WAFER**

80,698

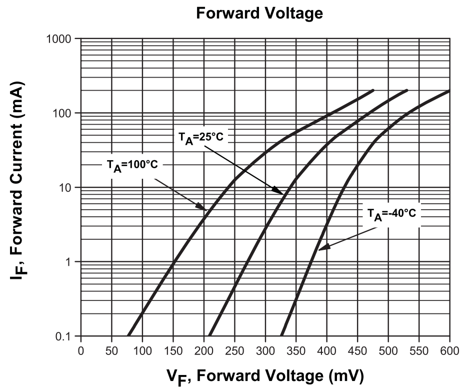
**PRINCIPAL DEVICE TYPES**

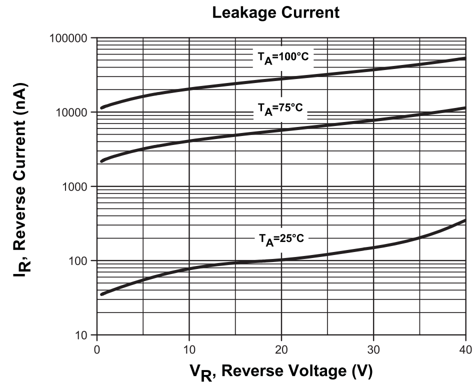
CFSH2-4L

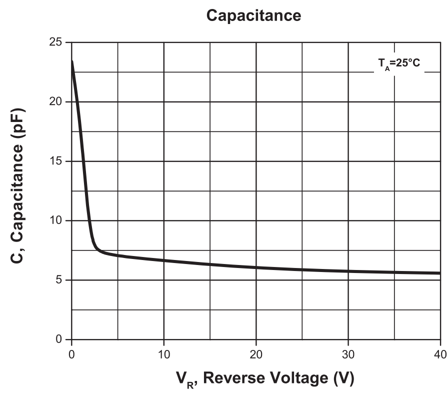
R1 (22-March 2010)

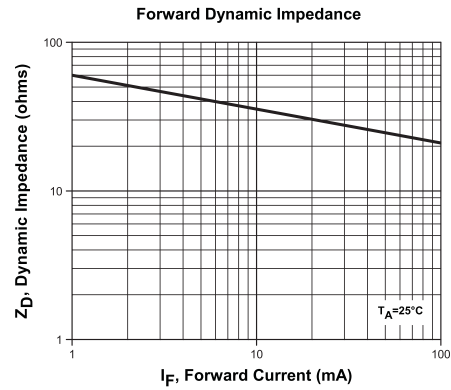
# PROCESS CPD87R

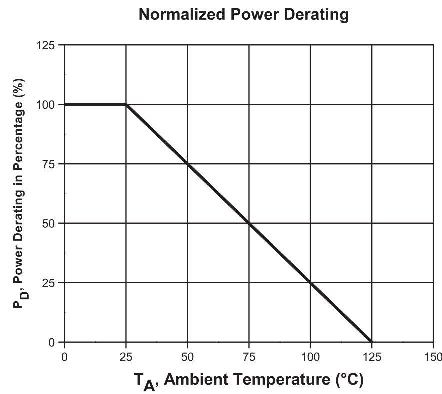
## Typical Electrical Characteristics




R1 (22-March 2010)